

Product Standards

PGA26E19BA

| | | | |
|--------------------|--------------------------------|---------|----------|
| Type | GaN-Tr | | |
| Application | For power switching | | |
| Structure | N-channel enhancement mode FET | | |
| Equivalent Circuit | Figure 1 | | |
| Out Line | DFN 8X8 | Marking | PGA26E19 |

A. ABSOLUTE MAXIMUM RATINGS (T_j = 25 °C , unless otherwise specified)

| No. | Item | Symbol | Values | | | Unit | Note |
|-----|---|------------------|--------|------|------|------|--|
| | | | Min. | Typ. | Max. | | |
| 1 | Drain-source voltage (DC) *1 | VDSS | - | - | 600 | V | |
| 2 | Drain-source voltage (pulse) *2 | VDSP | - | - | 750 | V | |
| 3 | Gate-source voltage (DC) *1 | VGSS | -10 | - | - | V | *VGSS+ is given by IG ratings *See application note |
| 4 | Gate current (DC) *1 | IG | - | - | 19 | mA | *See application note |
| 5 | Gate current (pulse) *3,4 | IGP | - | - | 0.6 | A | *See application note |
| 6 | Electric gate charge (pulse) | QGP | - | - | 12 | nC | *f=200kHz *See application note |
| 7 | Drain current (DC) (T _c = 25 °C) *1 | ID | - | - | 13 | A | Figure 4 |
| 8 | Drain reverse current (DC) (T _c = 25 °C) *1 | IDR | - | - | 13 | A | |
| 9 | Drain current (pulse) *5 (T _c = 25 °C) *1 | ID pulse | - | - | 23 | A | Figure 4 |
| 10 | Drain reverse current (pulse) *5 (T _c = 25 °C) *1 | IDR pulse | - | - | 23 | A | |
| 11 | Power dissipation (T _c = 25 °C) | PD | - | - | 66 | W | Figure 2 |
| 12 | Junction temperature | T _j | - | - | 150 | °C | |
| 13 | Storage temperature | T _{stg} | -55 | - | 150 | °C | |
| 14 | Drain-source voltage slope | dv/dt | - | - | 200 | V/ns | |

[Special instructions]

*1 : Please use this product to meet a condition of T_j within 150 °C.

*2 : Spike duty cycle D < 0.1, spike duration < 1us, total spike time < 1hour.

*3 : IGP is defined as (V_{cc} - V_{plateau}) / R_{gon}, as shown in Figure A.

V_{plateau} is the voltage between Gate and Source1.

*4 : Please use this product to meet both a maximum gate current and a maximum gate pulse charge of IGP(0.6A) and Q(12nC) respectively, as shown in Figure H.

*5 : Pulse width limited by T_{jmax}.

B. ELECTRICAL CHARACTERISTICS (T_j = 25 °C , unless otherwise specified)

| No. | Item | Symbol | Measurement Condition | Min. | Typ. | Max. | Unit |
|-----|--|---------|---|--|------|------|------|
| 1 | Drain cut-off current | IDSS | VDS=600 V, VGS=0 V, T _j =25 °C | - | - | 39 | μA |
| | | | VDS=600 V, VGS=0 V, T _j =150 °C | - | 39 | - | μA |
| 2 | Gate-source leakage current | IGSS | VGS=-3 V VDS=0 V | -1 | - | - | μA |
| 3 | Gate forward voltage | VGSF | IGS=10 mA open drain | 2.8 | 3.5 | 4.2 | V |
| 4 | Gate threshold voltage | VTH | VDS=10 V IDS=1 mA | 0.9 | 1.2 | 1.6 | V |
| 5 | Drain-source on-state resistance | RDS(on) | IGS=10 mA, IDS=5 A, T _j =25 °C | - | 140 | 190 | mΩ |
| | | | IGS=10 mA, IDS=5 A, T _j =150 °C | - | 290 | - | mΩ |
| 6 | Gate resistance | RG | f=100MHz open drain | - | 0.8 | - | Ω |
| 7 | Transfer conductance | gfs | VDS=8 V IDS=5 A | - | 15 | - | S |
| 8 | Input capacitance | Ciss | VDS=400 V VGS=0 V f=1 MHz | - | 160 | - | pF |
| 9 | Output capacitance | Coss | | - | 28 | - | pF |
| 10 | Reverse transfer capacitance | Crss | | - | 0.2 | - | pF |
| 11 | Turn-on delay time | td(on) | | VDD=400 V IDS=5 A (Figure A, Figure B) | - | 3.4 | - |
| 12 | Rise time | tr | V _{cc} =12 V R _{gon} =15 Ω, R _{goff} =4.7 Ω, R _{ig} =1500 Ω, C _s =680 pF | - | 5.2 | - | ns |
| 13 | Turn-off delay time | td(off) | | - | 3.4 | - | ns |
| 14 | Fall time | tf | | - | 2.4 | - | ns |
| 15 | Effective output capacitance (energy related) | Co(er) | VDS=0-480 V | - | 33 | - | pF |
| 16 | Effective output capacitance (time related) | Co(tr) | | - | 37 | - | pF |

C. GATE CHARGE CHARACTERISTICS (T_j = 25 °C, unless otherwise specified)

| No. | Item | Symbol | Measurement Condition | Min. | Typ. | Max. | Unit |
|-----|----------------------|-----------|--|------|------|------|------|
| 1 | Gate charge | Qg | VDD=400 V IDS=5 A (Figure C, Figure D) | - | 2.0 | - | nC |
| 2 | Gate-source charge | Qgs | | - | 0.3 | - | nC |
| 3 | Gate-drain charge | Qgd | | - | 1.0 | - | nC |
| 4 | Gate plateau voltage | V plateau | VDD=400 V IDS=5 A | - | 1.8 | - | V |

D. REVERSE CONDUCTING CHARACTERISTICS (T_j = 25 °C, unless otherwise specified)

| No. | Item | Symbol | Measurement Condition | Min. | Typ. | Max. | Unit |
|-----|-------------------------------|--------|-----------------------|------|------|------|------|
| 1 | Source-drain forward voltage | VSD | VGS=0 V ISD=5 A | - | 2.6 | - | V |
| 2 | Reverse recovery charge | Qrr | VDS=400 V ISD=5 A | - | 0 | - | nC |
| 3 | Reverse recovery time | trr | | - | 0 | - | ns |
| 4 | Peak reverse recovery current | Irrm | | - | 0 | - | A |
| 5 | Output charge | Qoss | | - | 17 | - | nC |
| | | | | | | | |

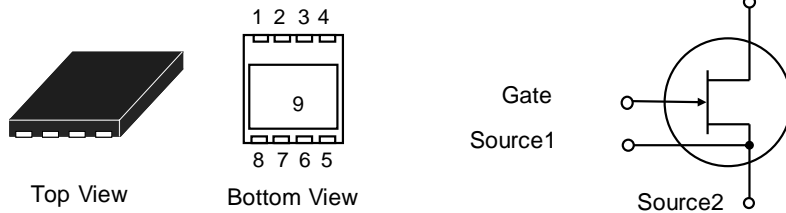
E. THERMAL RESISTANCE CHARACTERISTICS

| No. | Item | Symbol | Measurement Condition | Min. | Typ. | Max. | Unit |
|-----|--|----------|-----------------------|------|------|------|------|
| 1 | Thermal resistance (junction to case) | Rth(j-c) | | - | - | 1.9 | °C/W |
| 2 | Thermal resistance (junction to ambient) *1 | Rth(j-a) | | - | - | 46 | °C/W |
| 3 | Reflow soldering temperature | Tsold | reflow MSL3 | - | - | 260 | °C |

[Notes]

*1 : Device mounted on four layers epoxy PCB (6.45 cm² copper area and 70 μm thickness).

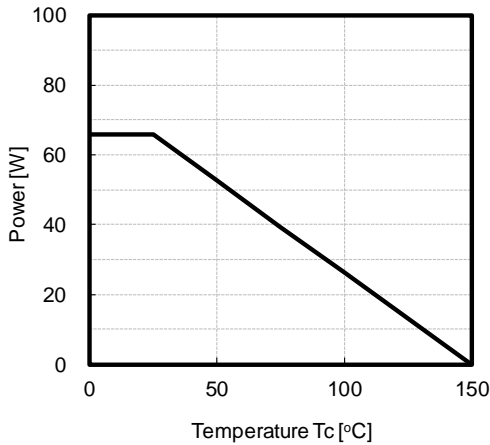
■ Equivalent circuit / Electrical characteristics



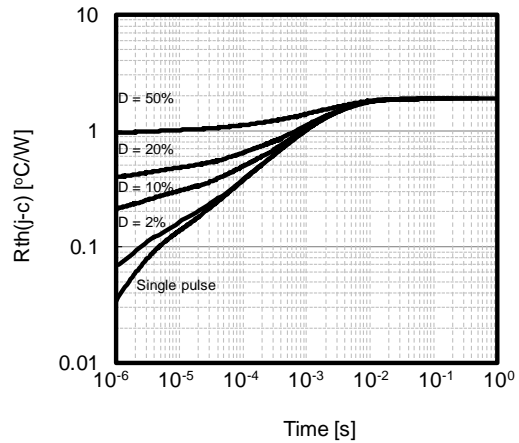
- 1,2,3,4 : Drain
- 5,6,9 : Source2
- 7 : Source1
- 8 : Gate

Notice:
Please connect Source1 pin to gate driver.

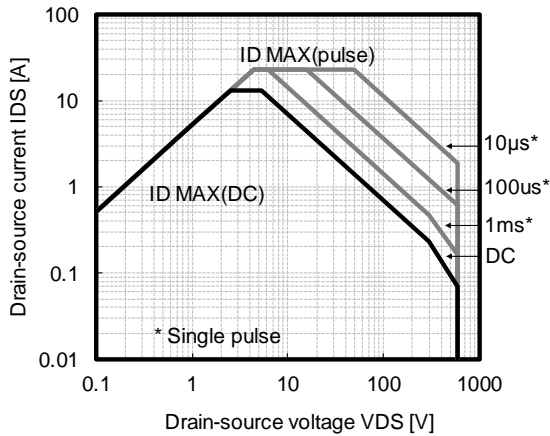
【Figure 1: Pin layout / Equivalent circuit】



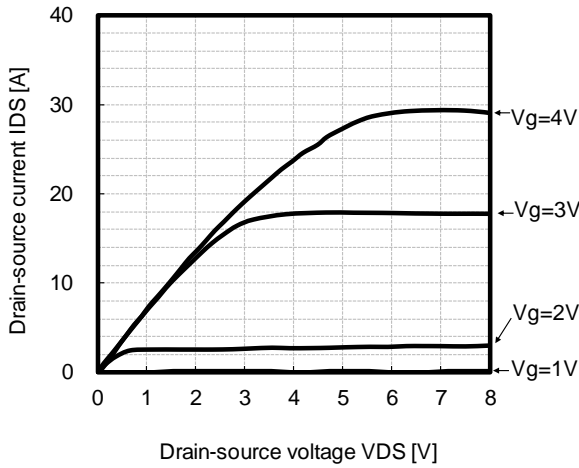
【Figure 2: Max. power dissipation】



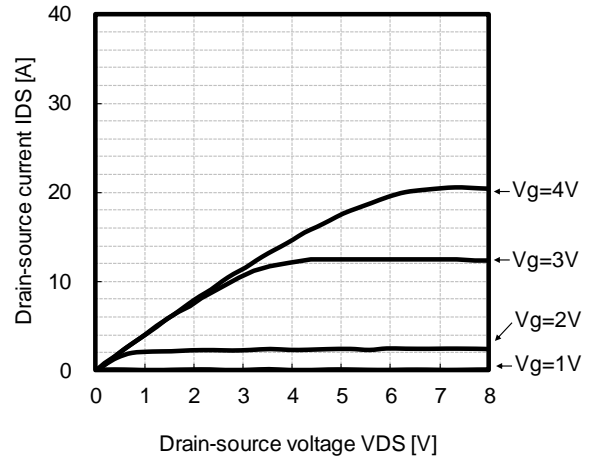
【Figure 3 : Transient thermal impedance】



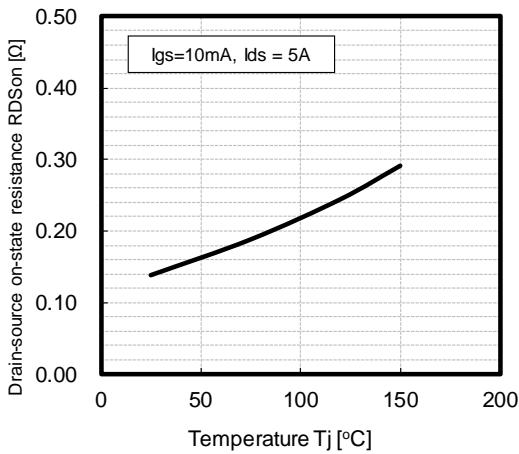
【Figure 4: Safe operating area Tc = 25 °C】



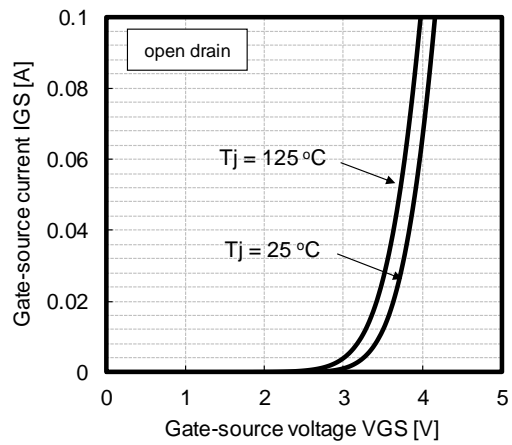
【Figure.5:Output characteristics Tc=25°C】



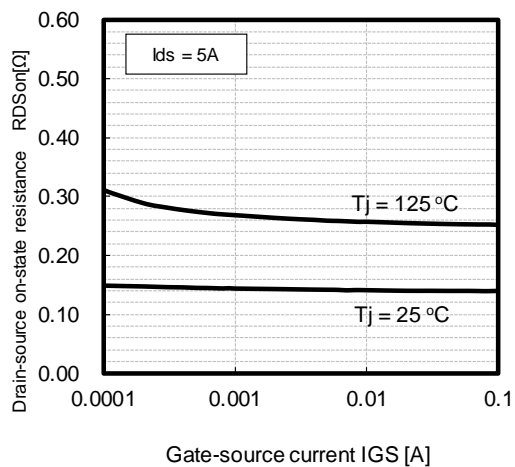
【Figure.6:Output characteristics Tc=125°C】



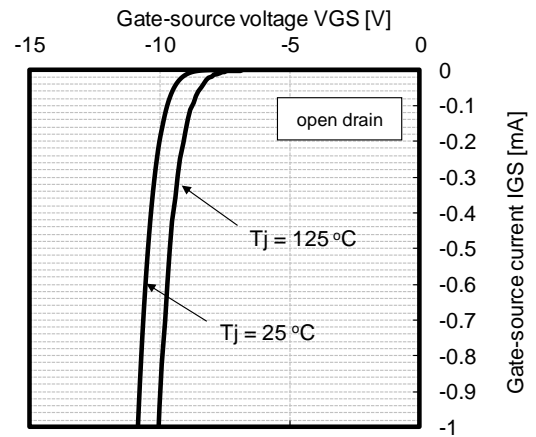
【Figure 7:Drain-source on-state resistance(RDS(on)-Tj)】



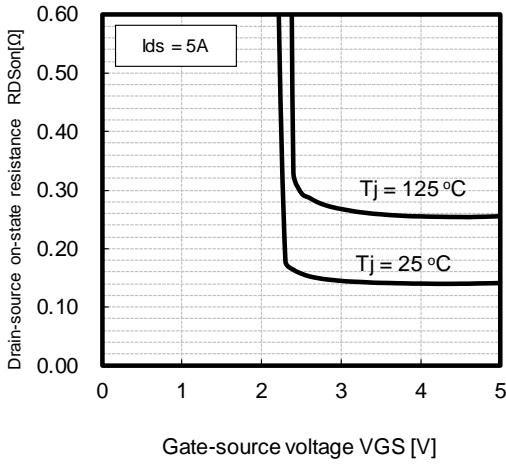
【Figure 8:Gate characteristics】



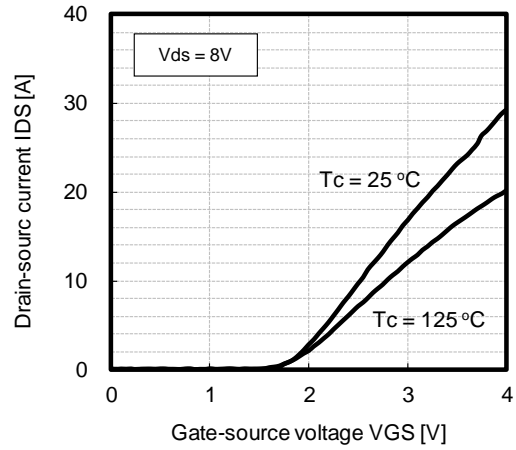
【Figure 9:Drain-source on-state resistance(RDS(on)-IGS)】



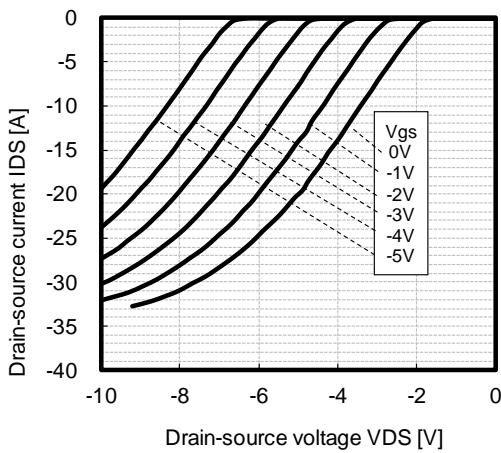
【Figure.10:Gate characteristics】



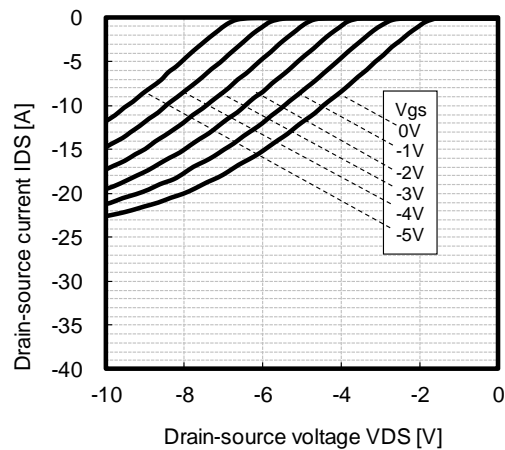
【Figure 11: Drain-source on-state resistance(RDS(on))-VGS】



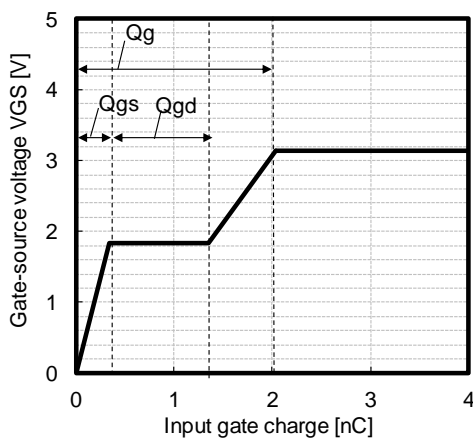
【Figure 12: Transfer characteristics】



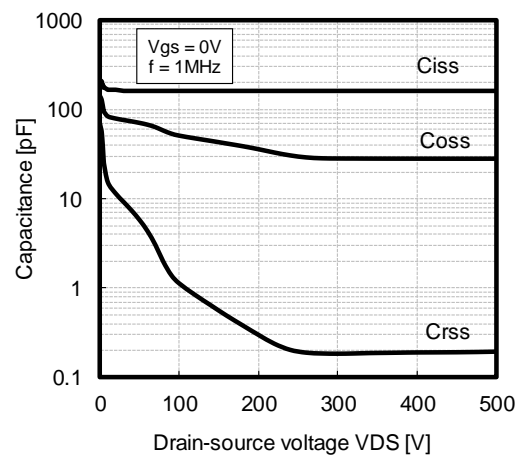
【Figure 13: Reverse channel characteristics (Tc=25°C)】



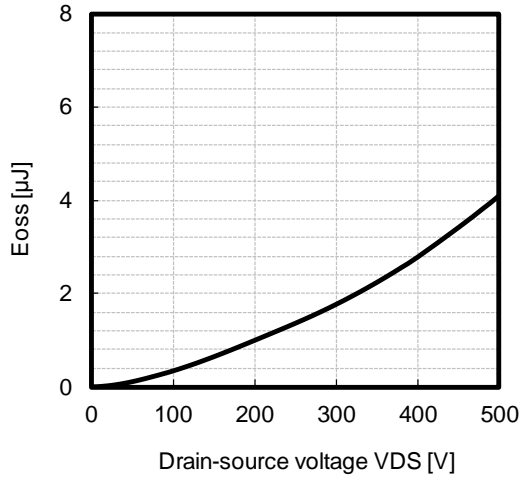
【Figure 14: Reverse channel characteristics (Tc=125°C)】



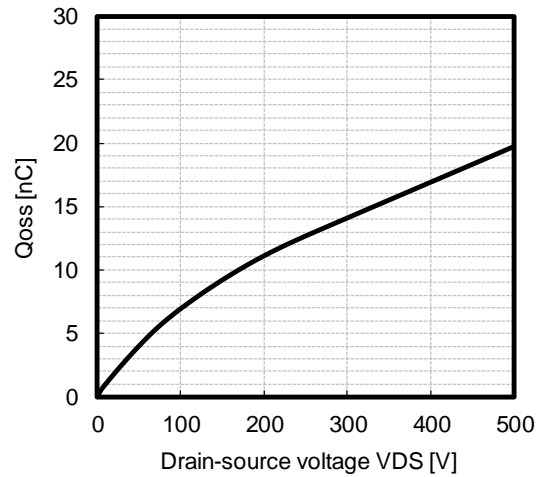
【Figure 15: Gate charge characteristics】



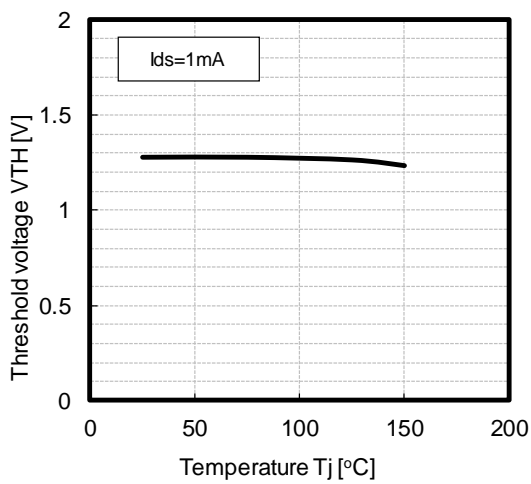
【Figure 16: Capacitance characteristics】



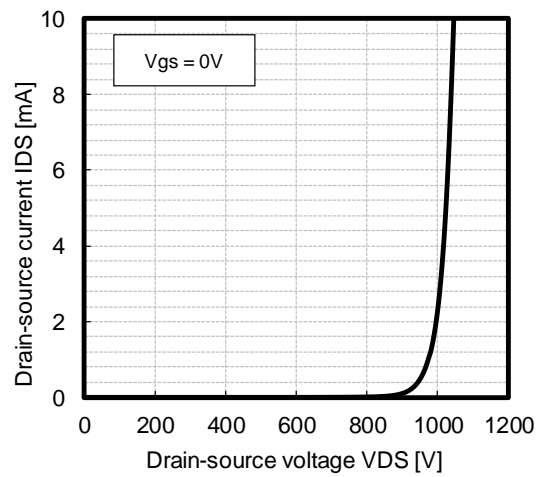
【Figure 17:Output capacitance stored energy】



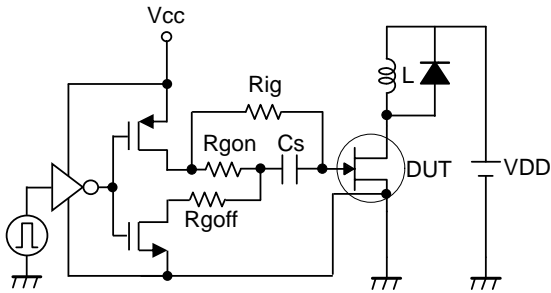
【Figure 18:Output charge】



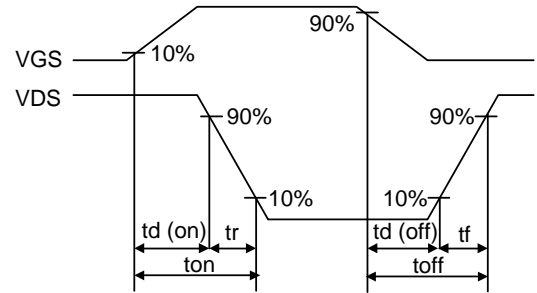
【Figure.19:Threshold voltage (VTH-Tj)】



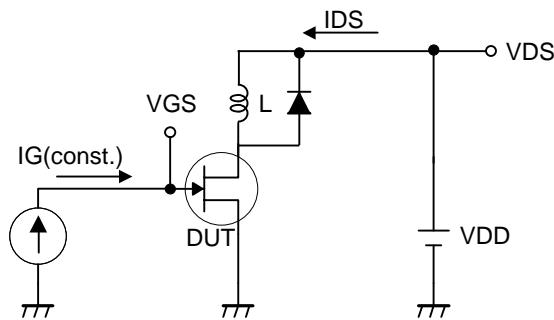
【Figure.20:Drain-Source leakage current (Tc=25°C)】



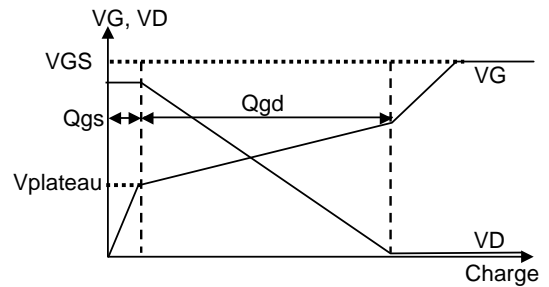
【Figure A : Switching time measurement】



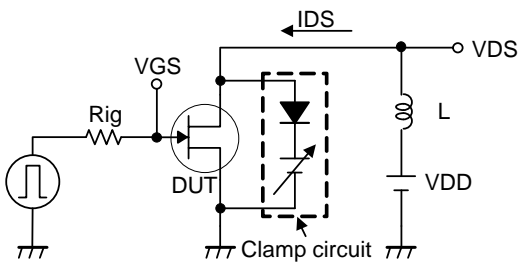
【Figure B : Switching wave form】



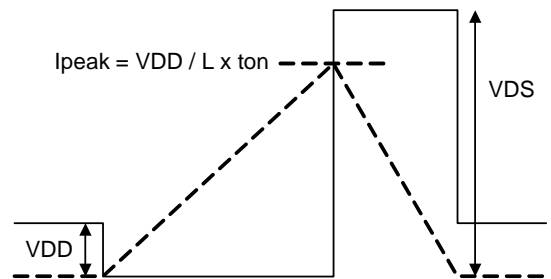
【Figure C : Gate charge measurement】



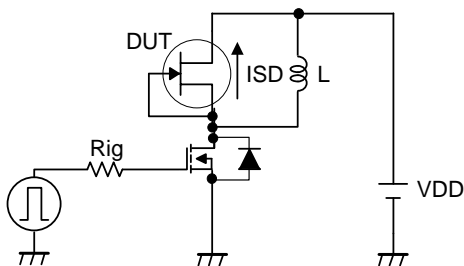
【Figure D : Gate charge wave form】



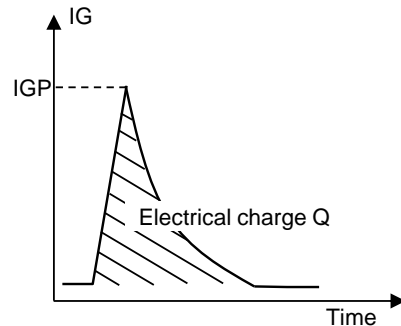
【Figure E : Reverse bias safe operating area dv/dt measurement circuit】



【Figure F : Reverse bias safe operating area dv/dt wave form】



【Figure G : di/dt measurement circuit】



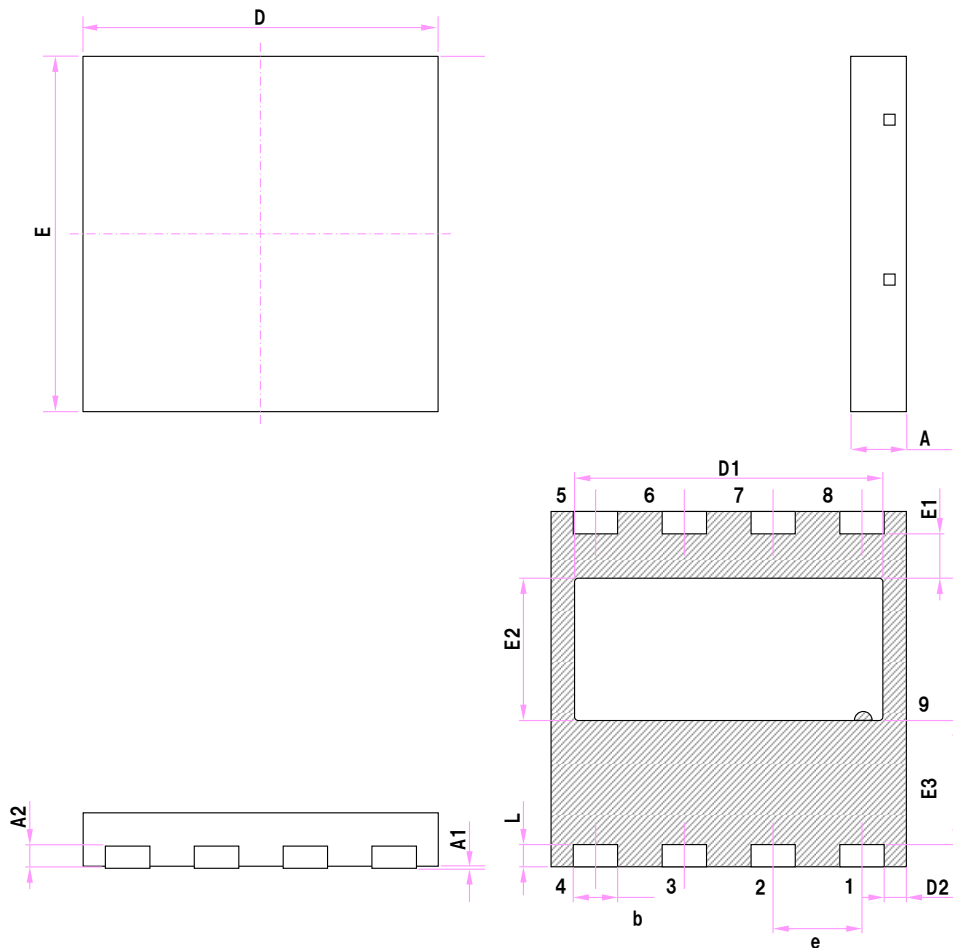
【Figure H : IGP wave form】

[Precautions for Use]

- 1) The product has risks for break-down or burst or giving off smoke in following conditions. Avoid the following use. Fuse should be added at the input side or connect zener diode between Gate pin and GND, etc as a countermeasure to pass regulatory Safety Standard. Concrete countermeasure could be provided individually. However, customer should make the final judgment.
 - (1) Reverse the Drain pin and gate pin connection to the power supply board.
 - (2) Drain pin short to Source1 pin and Source2 pin.
 - (3) Drain pin short to Gate pin.
 - (4) Gate pin open.
- 2) This product is under development and is subject to change without notice standards.

■ Outline

Unit: mm



| SYMBOL | DIMENSION | | |
|--------|-------------|------|------|
| | MIN | NOM | MAX |
| A | 1.15 | 1.25 | 1.35 |
| A1 | 0.00 | 0.02 | 0.05 |
| A2 | 0.40 | 0.50 | 0.60 |
| b | 0.90 | 1.00 | 1.10 |
| D | 7.90 | 8.00 | 8.10 |
| D1 | 6.84 | 6.94 | 7.04 |
| D2 | 0.40 | 0.50 | 0.60 |
| E | 7.90 | 8.00 | 8.10 |
| E1 | 0.90 | 1.00 | 1.10 |
| E2 | 3.10 | 3.20 | 3.30 |
| E3 | 2.70 | 2.80 | 2.90 |
| e | 2.00 B.S.C. | | |
| L | 0.40 | 0.50 | 0.60 |

*Please note that technical specifications are subject to change without notice.

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